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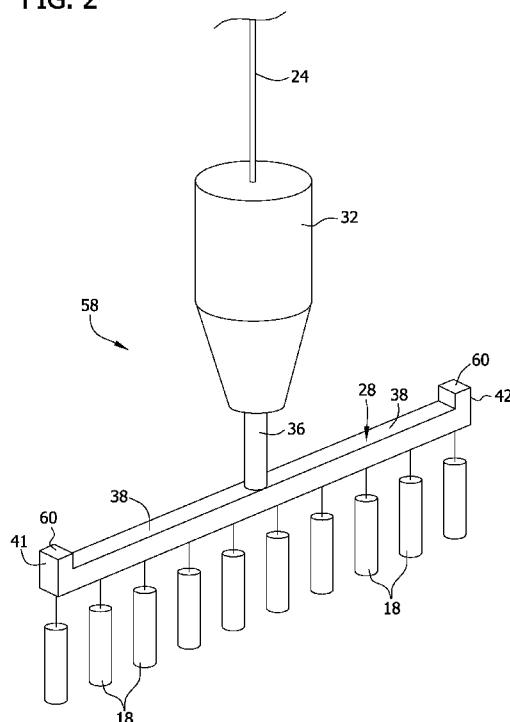
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(54) Title: METHODS AND PULLING ASSEMBLIES FOR PULLING A MULTICRYSTALLINE SILICON INGOT FROM A SILICON MELT

FIG. 2



(57) Abstract: Methods for producing multicrystalline silicon ingots by use of a Czochralski-type crystal puller and pulling assemblies that include a plurality of seed crystals for pulling multicrystalline silicon ingots.



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